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(54) Title: SURFACE TREATMENT FOR MULTI-LAYER WAFERS FORMED FROM LAYERS OF MATERIALS CHOSEN FROM AMONG SEMICONDUCTING MATERIALS

(57) Abstract: This invention relates to a process for treatment of a multi-layer wafer with materials having differential thermal characteristics, the process comprising a high temperature heat treatment step that can generate secondary defects, characterised in that this process includes a wafer surface preparation step before the high temperature heat treatment step.

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